



**CHENMKO ENTERPRISE CO.,LTD**

Halogens free devices

**SURFACE MOUNT  
PNP Switching Transistor**

VOLTAGE 20 Volts CURRENT 3 Ampere

**CHT5889GP**

**FEATURE**

- \* Small surface mounting type. (SOT-23)
- \* Low Collector-Emitter saturation voltage.

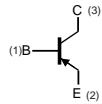
**CONSTRUCTION**

- \* PNP Silicon Transistor

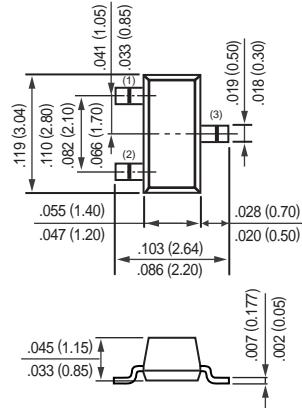
**MARKING**

- \* 5889

**CIRCUIT**



**SOT-23**



Dimensions in millimeters

**SOT-23**

**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CBO}$	collector-base voltage	open emitter	—	-20	V
$V_{CEO}$	collector-emitter voltage	open base	—	-20	V
$V_{EBO}$	emitter-base voltage	open collector	—	-7	V
$I_c$	collector current DC		—	-3.0	A
$I_{CP}$	collector current (Pulse)		—	-5.0	A
$I_B$	base current		—	-0.3	A
$P_{tot}$	total power dissipation	$T_{amb} \leq 25^\circ\text{C}$ ; note 1	—	460	mW
$T_{stg}$	storage temperature		-55	+150	°C
$T_j$	junction temperature		—	150	°C

**Note**

1. FR-4 @  $100\text{mm}^2$ , 1 oz. copper traces.

2008-01

## RATING CHARACTERISTIC CURVES ( CHT5889GP )

### ELECTRICAL CHARACTERISTICS

$T_{amb} = 25^{\circ}\text{C}$  unless otherwise noted.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$BV_{CBO}$	collector-base breakdown voltage	$I_E = 0; I_C = -100 \mu\text{A}$	-20	-	V
$BV_{CEO}$	collector-emitter breakdown voltage	$I_B = 0; I_C = -10 \text{ mA}$	-20	-	V
$BV_{EBO}$	emitter-base breakdown voltage	$I_C = 0; I_E = -100 \mu\text{A}$	-7	-	V
$I_{CBO}$	collector cut-off current	$I_E = 0; V_{CB} = - 20 \text{ V}$	-	-100	nA
$I_{EBO}$	emitter cut-off current	$I_C = 0; V_{EB} = - 7 \text{ V}$	-	-100	nA
$h_{FE}$	DC current gain	$V_{CE} = -2 \text{ V}; I_C = -500 \text{ mA}$ $V_{CE} = -2 \text{ V}; I_C = -1600 \text{ mA}$	200 100	500 -	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = -1600 \text{ mA}, I_B = -53 \text{ mA}$	-	-190	mV
$V_{BEsat}$	base-emitter saturation voltage	$I_C = -1600 \text{ mA}, I_B = -53 \text{ mA}$	-	-1.1	V
$C_c$	collector capacitance	$I_E = i_e = 0; V_{CB} = -10 \text{ V}; f = 1 \text{ MHz}$	-	40 <sub>Typ.</sub>	pF
$f_T$	transition frequency	$I_E = 500 \text{ mA}; V_{CE} = - 2 \text{ V};$	-	160 <sub>Typ.</sub>	MHz

## RATING CHARACTERISTIC CURVES ( CHT5889GP )

Figure 1. Grounded Emitter Propagation Characteristics

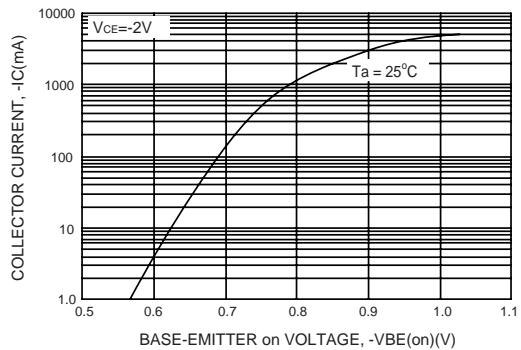


Figure 2. Collector-Emitter Saturation Voltage vs Collector Current

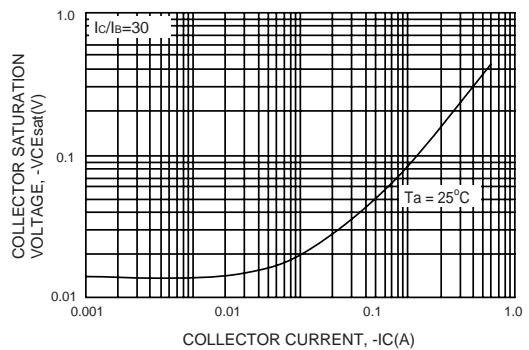


Figure 3. DC Current Gain

